

Title (en)

IMPROVED ENHANCEMENT LAYER FOR ELECTROPHOTOGRAPHIC DEVICES AND METHOD FOR DECREASING CHARGE FATIGUE THROUGH THE USE OF SAID LAYER

Publication

EP 0212581 A3 19880928 (EN)

Application

EP 86111267 A 19860814

Priority

US 76910685 A 19850826

Abstract (en)

[origin: EP0212581A2] An improved enhancement layer (18) operatively disposed between the top protective layer (19) and the photoconductive layer (16) of an electrophotographic device (10). The enhancement layer (18) is specifically tailored from a semiconductor alloy material designed to substantially prevent charge carriers from being caught in deep midgap traps as said carriers move toward the surface of the electrophotographic device (10) from the photoconductive layer (16) thereof. A method of substantially improving charge fatigue characteristics through the use of such an improved enhancement layer (18) is also disclosed.

IPC 1-7

G03G 5/082

IPC 8 full level

G03G 5/08 (2006.01); **G03G 5/082** (2006.01)

CPC (source: EP)

G03G 5/08235 (2013.01)

Citation (search report)

- [Y] EP 0137516 A2 19850417 - SHARP KK [JP]
- [A] EP 0141664 A2 19850515 - XEROX CORP [US]
- [A] US 4418132 A 19831129 - YAMAZAKI SHUNPEI [JP]
- [A] EP 0151754 A2 19850821 - ENERGY CONVERSION DEVICES INC [US]
- [A] US 4471042 A 19840911 - KOMATSU TOSHIYUKI [JP], et al
- [A] GB 2145530 A 19850327 - SHARP KK
- [Y] PATENT ABSTRACTS OF JAPAN, vol. 7, no. 188 (P-217)[1333], 17th August 1983; & JP-A-58 088 753 (OKI DENKI KOGYO K.K.) 26-05-1983

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